

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

# 2SJ338

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

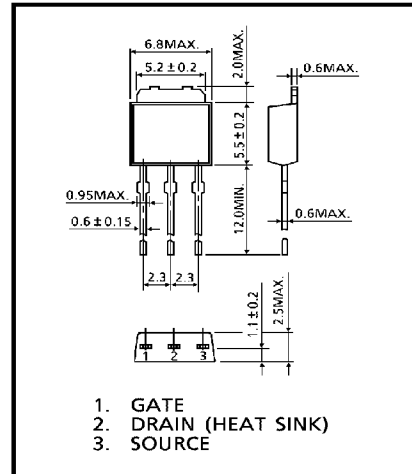
INDUSTRIAL APPLICATIONS

- High Breakdown Voltage :  $V_{DSS} = -180V$
- High Forward Transfer Admittance :  $|Y_{fs}| = 0.7S$  (Typ.)
- Complementary to 2SK2162

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

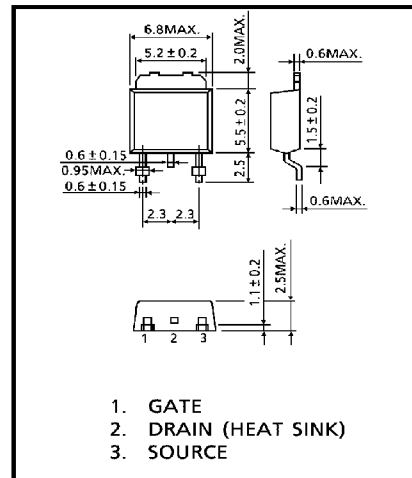
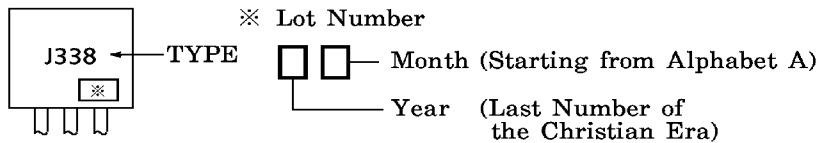
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	-180	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	-1	A
Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	20	W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

Unit in mm



JEDEC	—
EIAJ	SC-64
TOSHIBA	2-7B1B

MARKING



JEDEC	—
EIAJ	SC-64
TOSHIBA	2-7B2B

Weight : 0.36g

961001EAA2

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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0, V <sub>GS</sub> =±20V	—	—	±100	nA
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-10mA, V <sub>GS</sub> =0	-180	—	—	V
Gate-Source Cut-off Current	V <sub>GS(OFF)</sub> (Note)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-10mA	-0.8	—	-2.8	V
Drain-Source Saturation Voltage	V <sub>DS(ON)</sub>	I <sub>D</sub> =-0.6A, V <sub>GS</sub> =-10V	—	-1.2	-3.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.3A	—	0.7	—	S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0, f=1MHz	—	210	—	pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0, f=1MHz	—	90	—	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0, f=1MHz	—	45	—	pF

(Note) V<sub>GS(OFF)</sub> Classification    O : -0.8~-1.6,    Y : -1.4~-2.8

**This transistor is the electrostatic sensitive device.  
Please handle with caution.**